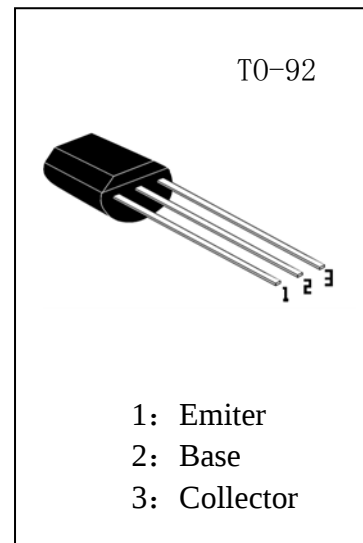


低压晶体管

- 集电极电流 $I_c=500\text{mA}$
- 高耗散功率 $P_c=625\text{mW}$
- 与 S8550 对管

极限参数(Absolute Maximum Ratings) $T_a=25^\circ\text{C}$

Characteristic	Symbol	Rating	Unit
Collector-Base Voltage	V_{cbo}	40	V
Collector-Emitter Voltage	V_{ceo}	25	V
Emitter-Base Voltage	V_{ebo}	5	V
Collector Current	I_c	500	mA
Collector Dissipation	P_c	625	m W
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55~150	$^\circ\text{C}$



电性能(Electrical Characteristic) $T_a=25^\circ\text{C}$

Symbol	Characteristic	Test Condition	Min	Typ	Max	Unit
BV_{cbo}	Collector-Base Breakdown Voltage	$I_c=100\mu\text{A}$ $I_e=0$	40			V
BV_{ceo}	Collector-Emitter Breakdown Voltage	$I_c=1\text{mA}$ $I_b=0$	25			V
BV_{ebo}	Emitter-Base Breakdown Voltage	$I_e=100\mu\text{A}$ $I_c=0$	5			V
I_{cbo}	Collector Cutoff Current	$V_{cb}=25\text{V}$, $I_e=0$			100	nA
I_{ebo}	Emitter Cutoff Current	$V_{eb}=3\text{V}$, $I_c=0$			100	nA
I_{ceo}	Collector Cutoff Current	$V_{ce}=20\text{V}$, $I_b=0$			10	μA
$V_{ce(sat)}$	Collector-Emitter Saturation Voltage	$I_c=500\text{mA}$, $I_b=50\text{mA}$		0.26	0.6	V
$V_{be(sat)}$	Base-Emitter Saturation Voltage	$I_c=500\text{mA}$, $I_b=50\text{mA}$		0.98	1.2	V
$V_{be(on)}$	Base-Emitter On Voltage	$V_{ce}=1\text{V}$, $I_c=10\text{mA}$	0.6	0.67	0.7	V
H_{fe1}	DC Current Gain	$V_{ce}=1\text{V}$, $I_c=50\text{mA}$	120		500	
H_{fe2}	DC Current Gain	$V_{ce}=1\text{V}$, $I_c=500\text{mA}$	30			

CLASS	C	D				
Hfe1	120-200	200-250	250-300	200-300	300-400	400-500